TLC27M2, TLC27M2A, TLC27M2B, TLC27M7 LinCMOS™ PRECISION DUAL OPERATIONAL AMPLIFIERS

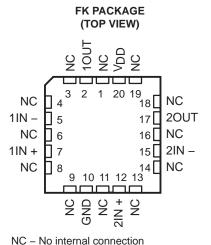
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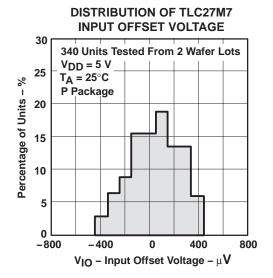
- Trimmed Offset Voltage: TLC27M7 . . . 500 μV Max at 25°C, V_{DD} = 5 V
- Input Offset Voltage Drift . . . Typically
 0.1 μV/Month, Including the First 30 Days
- Wide Range of Supply Voltages Over Specified Temperature Ranges:

0°C to 70°C . . . 3 V to 16 V -40°C to 85°C . . . 4 V to 16 V -55°C to 125°C . . . 4 V to 16 V

- Single-Supply Operation
- Common-Mode Input Voltage Range Extends Below the Negative Rail (C-Suffix, I-Suffix Types)

- Low Noise . . . Typically 32 nV/√Hz at f = 1 kHz
- Low Power . . . Typically 2.1 mW at 25°C,
 V_{DD} = 5 V
- Output Voltage Range Includes Negative Rail
- High Input impedance . . . $10^{12} \Omega$ Typ
- ESD-Protection Circuitry
- Small-Outline Package Option Also Available in Tape and Reel
- Designed-In Latch-Up Immunity





AVAILABLE OPTIONS

	V			PACKAGE		
TA	V _{IO} max AT 25°C	SMALL OUTLINE (D)	CHIP CARRIER (FK)	CERAMIC DIP (JG)	PLASTIC DIP (P)	TSSOP (PW)
	500 μV	TLC27M7CD	_	_	TLC27M7CP	_
000 1- 7000	2 mV	TLC27M2BCD	_	_	TLC27M2BCP	_
0°C to 70°C	5 mV	TLC27M2ACD	_	_	TLC27M2ACP	_
	10 mV	TLC27M2CD	_	_	TLC27M2CP	TLC27M2CPW
	500 μV	TLC27M7ID	_	_	TLC27M7IP	_
4000 to 0500	2 mV	TLC27M2BID	_	_	TLC27M2BIP	_
-40°C to 85°C	5 mV	TLC27M2AID	_	_	TLC27M2AIP	_
	10 mV	TLC27M2ID	_	_	TLC27M2IP	TLC27M2IPW
−55°C to 125°C	500 μV	TLC27M7MD	TLC27M7MFK	TLC27M7MJG	TLC27M7MP	_
-55 C (0 125°C	10 mV	TLC27M2MD	TLC27M2MFK	TLC27M2MJG	TLC27M2MP	_

The D and PW package are available taped and reeled. Add R suffix to the device type (e.g., TLC27M7CDR). For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

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TLC27M2, TLC27M2A, TLC27M2B, TLC27M7 LinCMOS™ PRECISION DUAL OPERATIONAL AMPLIFIERS

SLOS051E - OCTOBER 1987 - REVISED AUGUST 2008

description

The TLC27M2 and TLC27M7 dual operational amplifiers combine a wide range of input offset voltage grades with low offset voltage drift, high input impedance, low noise, and speeds approaching that of general-purpose bipolar devices. These devices use Texas Instruments silicon-gate LinCMOS technology, which provides offset voltage stability far exceeding the stability available with conventional metal-gate processes.

The extremely high input impedance, low bias currents, and high slew rates make these cost-effective devices ideal for applications which have previously been reserved for general-purpose bipolar products, but with only a fraction of the power consumption. Four offset voltage grades are available (C-suffix and I-suffix types), ranging from the low-cost TLC27M2 (10 mV) to the high-precision TLC27M7 (500 μ V). These advantages, in combination with good common-mode rejection and supply voltage rejection, make these devices a good choice for new state-of-the-art designs as well as for upgrading existing designs.

In general, many features associated with bipolar technology are available on LinCMOS operational amplifiers, without the power penalties of bipolar technology. General applications such as transducer interfacing, analog calculations, amplifier blocks, active filters, and signal buffering are easily designed with the TLC27M2 and TLC27M7. The devices also exhibit low voltage single-supply operation, making them ideally suited for remote and inaccessible battery-powered applications. The common-mode input voltage range includes the negative rail.

A wide range of packaging options is available, including small-outline and chip-carrier versions for high-density system applications.

The device inputs and outputs are designed to withstand –100-mA surge currents without sustaining latch-up.

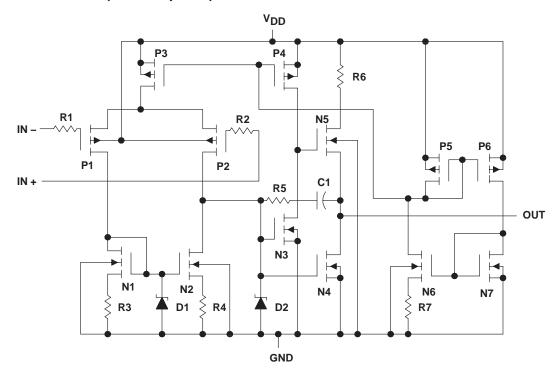
The TLC27M2 and TLC27M7 incorporate internal ESD-protection circuits that prevent functional failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015.2; however, care should be exercised in handling these devices as exposure to ESD may result in the degradation of the device parametric performance.

The C-suffix devices are characterized for operation from 0° C to 70° C. The I-suffix devices are characterized for operation from -40° C to 85° C. The M-suffix devices are characterized for operation over the full military temperature range of -55° C to 125° C.



SLOS051E - OCTOBER 1987 - REVISED AUGUST 2008

equivalent schematic (each amplifier)



TLC27M2, TLC27M2A, TLC27M2B, TLC27M7 LinCMOS[™] PRECISIÓN DUAL OPERATIONAL AMPLIFIERS

SLOS051E - OCTOBER 1987 - REVISED AUGUST 2008

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, V _{DD} (see Note 1)	18 V
Differential input voltage, V _{ID} (see Note 2)	
Input voltage range, V _I (any input)	
Input current, I ₁	
Output current, I _O (each output)	
Total current into V _{DD}	
Total current out of GND	
Duration of short-circuit current at (or below) 25°C (see Note 3)	Unlimited
Continuous total dissipation	
Operating free-air temperature, T _A : C suffix	0°C to 70°C
I suffix	–40°C to 85°C
M suffix	–55°C to 125°C
Storage temperature range	–65°C to 150°C
Case temperature for 60 seconds: FK package	260°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: D or P package	ge 260°C
Lead temperature 1,6 mm (1/16 inch) from case for 60 seconds: JG package	300°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, except differential voltages, are with respect to network ground.
 - 2. Differential voltages are at IN+ with respect to IN-.
 - 3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded (see application section).

DISSIPATION RATING TABLE

PACKAGE	$T_{\mbox{$A$}} \leq 25^{\circ}\mbox{$C$}$ POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING	T _A = 125°C POWER RATING
D	725 mW	5.8 mW/°C	464 mW	377 mW	
FK	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
JG	1050 mW	8.4 mW/°C	672 mW	546 mW	210 mW
Р	1000 mW	8.0 mW/°C	640 mW	520 mW	

recommended operating conditions

		C SU	FFIX	I SUF	FIX	M SUFFIX		
		MIN	MAX	MIN	MAX	MIN	MAX	UNIT
Supply voltage, V _{DD}		3	16	4	16	4	16	V
	V _{DD} = 5 V	-0.2	3.5	-0.2	3.5	0	3.5	\/
Common-mode input voltage, V _{IC}	V _{DD} = 10 V	-0.2	8.5	-0.2	8.5	0	8.5	V
Operating free-air temperature, TA		0	70	-40	85	-55	125	°C



TLC27M2, TLC27M2A, TLC27M2B, TLC27M7 LinCMOS™ PRECISION DUAL OPERATIONAL AMPLIFIERS

SLOS051E - OCTOBER 1987 - REVISED AUGUST 2008

electrical characteristics at specified free-air temperature, $V_{\mbox{\scriptsize DD}}$ = 5 V (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	T _A †	TL TL	.C27M2 .C27M2 .C27M2 .C27M7	AC BC	UNIT
						MIN	TYP	MAX	
		TLC27M2C	$V_0 = 1.4 \text{ V},$	$V_{IC} = 0$,	25°C		1.1	10	
			$R_S = 50 \Omega$,	$R_{\parallel} = 100 \text{ k}\Omega$	Full range			12	mV
		TLC27M2AC	$V_{O} = 1.4 \text{ V},$	$V_{IC} = 0$,	25°C		0.9	5	
VIO	Input offset voltage		$R_S = 50 \Omega$,	$R_{\parallel} = 100 \text{ k}\Omega$	Full range			6.5	
1.0		TLC27M2BC	$V_0 = 1.4 \text{ V},$	$V_{IC} = 0$,	25°C		220	2000	
		12027111280	$R_S = 50 \Omega$,	$R_{\parallel} = 100 \text{ k}\Omega$	Full range			3000	μV
		TLC27M7C	$V_0 = 1.4 \text{ V},$	$V_{IC} = 0$,	25°C		185	500	μν
			$R_S = 50 \Omega$,	$R_{\parallel} = 100 \text{ k}\Omega$	Full range			1500	
αΝΙΟ	Average temperature coeffset voltage	fficient of input			25°C to 70°C		1.7		μV/°C
	Lament office to a summer to the control of	1-1-4)	V 05V	., 05.,	25°C		0.1	60	A
lio	Input offset current (see N	iote 4)	$V_0 = 2.5 V$,	$V_{IC} = 2.5 V$	70°C		7	300	pA
	1 (1) (/ N		V 0.5.V	.,	25°C		0.6	60	
I _{IB}	Input bias current (see No	ite 4)	$V_0 = 2.5 V$,	$V_{IC} = 2.5 V$	70°C		40	600	pA
						-0.2	-0.3		
					25°C	to	to		V
VICR	Common-mode input volta (see Note 5)	age range				4	4.2		
ion	(See Note 5)				Full range	-0.2 to			V
					T dil rango	3.5			•
					25°C	3.2	3.9		
∨он	High-level output voltage		V _{ID} = 100 mV,	R _L = 100 kΩ	0°C	3	3.9		V
0				_	70°C	3	4		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	0°C		0	50	mV
02	, ,			02	70°C		0	50	
					25°C	25	170		
AVD	Large-signal differential vo	oltage	$V_0 = 0.25 \text{ V to 2 V},$	$R_I = 100 \text{ k}\Omega$	0°C	15	200		V/mV
'5	amplification			-	70°C	15	140		
					25°C	65	91		
CMRR	Common-mode rejection i	ratio	V _{IC} = V _{ICR} min		0°C	60	91		dB
	,				70°C	60	92		
					25°C	70	93		
ksvr	Supply-voltage rejection ra	atio	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_{O} = 1.4 \text{ V}$	0°C	60	92		dB
	$(\Delta V_{DD}/\Delta V_{IO})$			Ü	70°C	60	94		
					25°C		210	560	
I _{DD}	Supply current (two ampli	fiers)	$V_O = 2.5 \text{ V},$	$V_{IC} = 2.5 V,$	0°C		250	640	μΑ
		,	No load		70°C		170	440	

[†] Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



^{5.} This range also applies to each input individually.

TLC27M2, TLC27M2A, TLC27M2B, TLC27M7 LinCMOS™ PRECISION DUAL OPERATIONAL AMPLIFIERS

SLOS051E - OCTOBER 1987 - REVISED AUGUST 2008

electrical characteristics at specified free-air temperature, $V_{\mbox{\scriptsize DD}}$ = 10 V (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS	TAT	TL TL	.C27M20 .C27M2/ .C27M21 .C27M70	AC BC	UNIT
						MIN	TYP	MAX	
		TLC27M2C	$V_0 = 1.4 \text{ V},$	$V_{IC} = 0$	25°C		1.1	10	
		1202711120	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			12	mV
		TLC27M2AC	$V_{O} = 1.4 \text{ V},$	$V_{IC} = 0$,	25°C		0.9	5	
VIO	Input offset voltage	120271112710	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			6.5	
1 10	input onset voltage	TLC27M2BC	$V_0 = 1.4 \text{ V},$	$V_{IC} = 0$,	25°C		224	2000	
		TEGETWEBO	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			3000	μV
		TLC27M7C	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		190	800	μν
		TEOZYWYO	$R_S = 50 \Omega$	$R_L = 100 \text{ k}\Omega$	Full range			1900	
αΝΙΟ	Average temperature coe offset voltage	efficient of input			25°C to 70°C		2.1		μV/°C
					25°C		0.1	60	
IIO	Input offset current (see I	Note 4)	$V_O = 5 V$	$V_{IC} = 5 V$	70°C		7	300	pΑ
					25°C		0.7	60	
I _{IB}	Input bias current (see N	ote 4)	$V_{O} = 5 V,$	$V_{IC} = 5 V$	70°C		50	600	рA
						-0.2	-0.3		
ļ.,	Common-mode input volt	age range			25°C	to 9	to 9.2		V
VICR	(see Note 5)				Full range	-0.2 to 8.5			V
					25°C	8	8.7		
VOH	High-level output voltage		V _{ID} = 100 mV,	R _L = 100 kΩ	0°C	7.8	8.7		V
				_	70°C	7.8	8.7		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	0°C		0	50	mV
-				<u>-</u>	70°C		0	50	
					25°C	25	275		
AVD	Large-signal differential v	oltage	$V_0 = 1 \text{ V to 6 V},$	R _L = 100 kΩ	0°C	15	320		V/mV
'-	amplification			_	70°C	15	230		
					25°C	65	94		
CMRR	Common-mode rejection	ratio	V _{IC} = V _{ICR} min		0°C	60	94		dB
	,		.5 .5.		70°C	60	94		
					25°C	70	93		
k _{SVR}	Supply-voltage rejection	ratio	$V_{DD} = 5 \text{ V to } 10 \text{ V,}$	VO = 1.4 V	0°C	60	92		dB
""	$(\Delta V_{DD}/\Delta V_{IO})$		-	Ü	70°C	60	94		
					25°C		285	600	
I _{DD}	Supply current (two ampl	ifiers)	$V_O = 5 V$	$V_{IC} = 5 V$,	0°C		345	800	μΑ
	•		No load		70°C		220	560	

[†] Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



TLC27M2, TLC27M2A, TLC27M2B, TLC27M7 LinCMOS™ PRECISION DUAL OPERATIONAL AMPLIFIERS

SLOS051E - OCTOBER 1987 - REVISED AUGUST 2008

electrical characteristics at specified free-air temperature, $V_{\mbox{\scriptsize DD}}$ = 5 V (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS	TΑ [†]	TL TL	.C27M2 .C27M2 .C27M2 .C27M7	AI BI	UNIT
		_				MIN	TYP	MAX	
		TLC27M2I	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		1.1	10	
		TEOZITVIZI	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			13	mV
		TLC27M2AI	$V_{O} = 1.4 V$	$V_{IC} = 0$,	25°C		0.9	5	111.
VIO	Input offset voltage	TEOZIWIZI	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			7	
V10	input onset voltage	TLC27M2BI	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		220	2000	
		TEOZIWIZDI	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			3500	μV
		TLC27M7I	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		185	500	μν
		TEGZTIVITI	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			2000	
αΝΙΟ	Average temperature coef offset voltage	ficient of input			25°C to 85°C		1.7		μV/°C
			.,	.,	25°C		0.1	60	
lio	Input offset current (see N	ote 4)	$V_{O} = 2.5 \text{ V},$	$V_{IC} = 2.5 V$	85°C		24	1000	рA
			.,		25°C		0.6	60	
I _{IB}	Input bias current (see No	te 4)	$V_0 = 2.5 V$,	$V_{IC} = 2.5 V$	85°C		200	2000	рA
						-0.2	-0.3		
					25°C	to	to		V
VICR	Common-mode input volta (see Note 5)	age range				4	4.2		
ion	(See Note 5)				Full range	-0.2 to			V
					T dir range	3.5			·
					25°C	3.2	3.9		
∨он	High-level output voltage		V _{ID} = 100 mV,	$R_L = 100 \text{ k}\Omega$	-40°C	3	3.9		V
				_	85°C	3	4		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	-40°C		0	50	mV
02			"	02	85°C		0	50	
					25°C	25	170		
AVD	Large-signal differential vo	oltage	$V_0 = 0.25 \text{ V to 2 V},$	$R_I = 100 \text{ k}\Omega$	-40°C	15	270		V/mV
'	amplification		<u> </u>	_	85°C	15	130		
					25°C	65	91		
CMRR	Common-mode rejection r	atio	V _{IC} = V _{ICR} min		-40°C	60	90		dB
			.0 1010		85°C	60	90		
					25°C	70	93		
ksvr	Supply-voltage rejection ra	atio	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	V _O = 1.4 V	-40°C	60	91		dB
	$(\Delta V_{DD}/\Delta V_{IO})$		-	Ŭ	85°C	60	94		
					25°C		210	560	
I _{DD}	Supply current (two amplit	iers)	V _O = 2.5 V,	$V_{IC} = 2.5 V$,	-40°C		315	800	μΑ
		,	No load		85°C		160	400	,

[†] Full range is –40°C to 85°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



^{5.} This range also applies to each input individually.

TLC27M2, TLC27M2A, TLC27M2B, TLC27M7 LinCMOS™ PRECISION DUAL OPERATIONAL AMPLIFIERS

SLOS051E - OCTOBER 1987 - REVISED AUGUST 2008

electrical characteristics at specified free-air temperature, V_{DD} = 10 V (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	T _A †	TI TI	C27M2 C27M2 C27M2 C27M2	AI BI	UNIT
						MIN	TYP	MAX	
		TLC27M2I	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		1.1	10	
		TLG2/IVIZI	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			13	mV
		TLC27M2AI	$V_{O} = 1.4 V$	$V_{IC} = 0$,	25°C		0.9	5	IIIV
V _{IO}	Input offset voltage	TLOZIWIZAI	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			7	
V10	input onset voltage	TLC27M2BI	$V_0 = 1.4 V$	$V_{IC} = 0$,	25°C		224	2000	
		TEGETIVIZEDI	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			3500	μV
		TLC27M7I	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		190	800	μν
		TLOZIWITI	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			2900	
αΛΙΟ	Average temperature coeffice offset voltage	cient of input			25°C to 85°C		2.1		μV/°C
	lanut effect compat (a.e. Net	- 4\	V 5 V	V 5.V	25°C		0.1	60	A
IIO	Input offset current (see Not	e 4)	$V_{O} = 5 V,$	$V_{IC} = 5 V$	85°C		26	1000	рA
					25°C		0.7	60	
I _{IB}	Input bias current (see Note	4)	V _O = 5 V,	V _{IC} = 5 V	85°C		220	200	рА
	Common-mode input voltag	e range			25°C	-0.2 to 9	-0.3 to 9.2		V
VICR	(see Note 5)	Ū			Full range	-0.2 to 8.5			V
					25°C	8	8.7		
∨он	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 100 \text{ k}\Omega$	−40°C	7.8	8.7		V
					85°C	7.8	8.7		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	-40°C		0	50	mV
					85°C		0	50	
					25°C	25	275		
A _{VD}	Large-signal differential volta amplification	age	$V_0 = 1 \ V \ to 6 \ V,$	$R_L = 100 \text{ k}\Omega$	-40°C	15	390		V/mV
	ap				85°C	15	220		
					25°C	65	94		
CMRR	Common-mode rejection rat	io	V _{IC} = V _{ICR} min		−40°C	60	93		dB
					85°C	60	94		
	Supply-voltage rejection rati	0			25°C	70	93		
ksvr	(ΔVDD/ΔVIO)	U	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	-40°C	60	91		dB
	. 55 10/				85°C	60	94		
			\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	Vio - F.V	25°C		285	600	
IDD	Supply current		V _O = 5 V, No load	$V_{IC} = 5 V$	−40°C		450	900	μΑ
					85°C		205	520	

[†]Full range is -40°C to 85°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



TLC27M2, TLC27M2A, TLC27M2B, TLC27M7 LinCMOS™ PRECISION DUAL OPERATIONAL AMPLIFIERS

SLOS051E - OCTOBER 1987 - REVISED AUGUST 2008

electrical characteristics at specified free-air temperature, V_{DD} = 5 V (unless otherwise noted)

	PARAMETER		TEST CONDITIONS		T _A †		.C27M2I .C27M7I		UNIT
						MIN	TYP	MAX	
		TI 00714014	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	
.,	land offert valence	TLC27M2M	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			12	>/
V _{IO}	Input offset voltage	TI 00714714	V _O = 1.4 V,	V _{IC} = 0,	25°C		185	500	mV
		TLC27M7M	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			3750	
αΛΙΟ	Average temperature coeff offset voltage	icient of input			25°C to 125°C		1.7		μV/°C
	leavel offert comment (see Nie	. (- 4)	V 05V	.v. 0.5.v.	25°C		0.1	60	рА
lo	Input offset current (see No	ote 4)	$V_0 = 2.5 V$,	$V_{IC} = 2.5 V$	125°C		1.4	15	nA
	1 (1) (1) (1)		.,		25°C		0.6	60	рА
IВ	Input bias current (see Not	e 4)	$V_0 = 2.5 V$,	$V_{IC} = 2.5 V$	125°C		9	35	nA
	Common-mode input volta	ge range			25°C	0 to 4	-0.3 to 4.2		V
VICR	(see Note 5)				Full range	0 to 3.5			V
					25°C	3.2	3.9		
Vон	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 100 \text{ k}\Omega$	−55°C	3	3.9		V
					125°C	3	4		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	−55°C		0	50	mV
					125°C		0	50	
					25°C	25	170		
AVD	Large-signal differential vol amplification	tage	$V_0 = 0.25 \text{ V to 2 V},$	$R_L = 100 \text{ k}\Omega$	−55°C	15	290		V/mV
	amplification				125°C	15	120		
					25°C	65	91		
CMRR	Common-mode rejection ra	atio	V _{IC} = V _{ICR} min		−55°C	60	89		dB
					125°C	60	91		
					25°C	70	93		
k _{SVR}	Supply-voltage rejection ra (ΔV _{DD} /ΔV _{IO})	tio	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	V _O = 1.4 V	−55°C	60	91		dB
	ישטי≏י וט/				125°C	60	94		
					25°C		210	560	
I_{DD}	Supply current (two amplific	ers)	V _O = 2.5 V, No load	$V_{IC} = 2.5 V,$	−55°C		340	880	μΑ
			1.10 1000		125°C		140	360	

[†]Full range is –55°C to 125°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



TLC27M2, TLC27M2A, TLC27M2B, TLC27M7 LinCMOS™ PRECISION DUAL OPERATIONAL AMPLIFIERS

SLOS051E - OCTOBER 1987 - REVISED AUGUST 2008

electrical characteristics at specified free-air temperature, V_{DD} = 10 V (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	T _A †		1.1 10 12 190 800 4300	UNIT	
						MIN	TYP	MAX	
		TI 00714014	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	
.,		TLC27M2M	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			12	.,
VIO	Input offset voltage		V _O = 1.4 V,	V _{IC} = 0,	25°C		190	800	mV
		TLC27M7M	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			4300	
αΝΙΟ	Average temperature coeffice offset voltage	ient of input			25°C to 125°C		2.1		μV/°C
		٥	.,,		25°C		0.1	60	
ΙO	Input offset current (see Not	e 4)	$V_0 = 5 V$,	$V_{IC} = 5 V$	125°C		1.8	15	рA
					25°C		0.7	60	
IIB	Input bias current (see Note	4)	$V_0 = 5 V$,	$V_{IC} = 5 V$	125°C		10	35	рA
,,	Common-mode input voltage	e range			25°C	to	to		V
VICR	(see Note 5)				Full range	to			٧
					25°C	8	8.7		
Vон	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 100 \text{ k}\Omega$	−55°C	7.8	8.6		V
					125°C	7.8	8.8		
					25°C		0	50	
VOL	Low-level output voltage		$V_{1D} = -100 \text{ mV},$	$I_{OL} = 0$	−55°C		0	50	mV
					125°C		0	50	
					25°C	25	275		
AVD	Large-signal differential volta amplification	age	$V_0 = 1 \ V \ to 6 \ V,$	$R_L = 100 \text{ k}\Omega$	−55°C	15	420		V/mV
	amplification				125°C	15	190		
					25°C	65	94		
CMRR	Common-mode rejection rat	io	V _{IC} = V _{ICR} min		−55°C	60	93		dB
					125°C	60	93		
					25°C	70	93		
ksvr	Supply-voltage rejection rati (ΔV _{DD} /ΔV _{IO})	0	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	−55°C	60	91		dB
	(¬, DD, ¬, IO)				125°C	60	94		
					25°C		285	600	
IDD	Supply current (two amplifie	rs)	V _O = 5 V, No load	$V_{IC} = 5 V$	−55°C		490	1000	μΑ
			I NO IOAU		125°C		180	480	

[†]Full range is -55°C to 125°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.

TLC27M2, TLC27M2A, TLC27M2B, TLC27M7 LinCMOS™ PRECISION DUAL OPERATIONAL AMPLIFIERS

SLOS051E - OCTOBER 1987 - REVISED AUGUST 2008

operating characteristics at specified free-air temperature, $V_{DD} = 5 V$

	PARAMETER	TEST C	ONDITIONS	TA	TLC: TLC:	27M2C 27M2A 27M2B 27M7C	C C	UNIT	
					MIN	TYP	MAX		
				25°C		0.43			
			V _{I(PP)} = 1 V	0°C		0.46			
CD	Class note at waits agin	$R_L = 100 \text{ k}\Omega$		70°C		0.36		\//··•	
SR	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.40		V/μs	
		are right t		V _{I(PP)} = 2.5 V	0°C		0.43		
			, ,	70°C		0.34			
V _n	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$,	25°C		32		nV/√ Hz	
				25°C		55			
Вом	Maximum output-swing bandwidth	$V_O = V_{OH}$, $R_L = 100 \text{ k}\Omega$,		0°C		60		kHz	
			See rigule i	70°C		50			
				25°C		525			
В1	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	$C_L = 20 pF$,	0°C		600		kHz	
	,, 3	See Figure 3		70°C		400			
				25°C		40°			
φm	m Phase margin	$V_{l} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	f = B ₁ , See Figure 3	0°C		41°			
		OL = 20 με,	See Figure 3	70°C		39°			

operating characteristics at specified free-air temperature, V_{DD} = 10 V

	PARAMETER	TEST C	ONDITIONS	TA	TL(C27M2C C27M2A C27M2E C27M7C TYP	C SC	UNIT
				25°C	IVIIIN	0.62	IVIAA	
			V _{I(PP)} = 1 V	0°C		0.67		
		$R_L = 100 \text{ k}\Omega$,	'((FF) ' '	70°C		0.51		
SR	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.56		V/μs
		occ riguic r	V _{I(PP)} = 5.5 V	0°C		0.61		
			.(,	70°C		0.46		
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$,	25°C		32		nV/√ Hz
				25°C		35		
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH}$, $R_L = 100 \text{ k}\Omega$,	C _L = 20 pF, See Figure 1	0°C		40		kHz
			See Figure 1	70°C		30		
				25°C		635		
В1	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	$C_L = 20 pF$,	0°C		710		kHz
	om, gan sanaman	occ rigare o		70°C		510		
)/ 40 ···)/	, D	25°C		43°		
φm	Phase margin	$V_{l} = 10 \text{ mV},$ $C_{l} = 20 \text{ pF},$	f = B ₁ , See Figure 3	0°C		44°		
		2 20 pr,		70°C		42°		

TLC27M2, TLC27M2A, TLC27M2B, TLC27M7 LinCMOS™ PRECISION DUAL OPERATIONAL AMPLIFIERS

SLOS051E - OCTOBER 1987 - REVISED AUGUST 2008

operating characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$

	PARAMETER	TEST CO	ONDITIONS	TA	TL TL TL	UNIT			
			_		MIN	TYP	MAX		
				25°C		0.43			
			V _{I(PP)} = 1 V	−40°C		0.51			
		$R_L = 100 \text{ k}\Omega$		85°C		0.35		V/μs	
SR	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.40			
		ess i gara	V _{I(PP)} = 2.5 V	-40°C		0.48			
				85°C		0.32			
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$,	25°C		32		nV/√ Hz	
		$V_O = V_{OH}$, $R_1 = 100 \text{ k}\Omega$,		25°C		55			
ВОМ	Maximum output-swing bandwidth			-40°C		75		kHz	
			See rigule r	85°C		45			
				25°C		525			
B ₁	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	$C_L = 20 pF$,	−40°C		770		kHz	
		See Figure 3		85°C		370			
				25°C		40°			
φ _m Phase margin	Phase margin	$V_I = 10 \text{ mV},$ $C_L = 20 \text{ pF},$	f = B ₁ , See Figure 3	-40°C		43°			
		OL = 20 pr ,	occ rigule 3	85°C		38°			

operating characteristics at specified free-air temperature, V_{DD} = 10 V

	PARAMETER	TEST CO	ONDITIONS	TA	TL TL TL	UNIT		
					MIN	TYP	MAX	
				25°C		0.62		
			V _{I(PP)} = 1 V	-40°C	C 0.77			
	Olemante et militareira	$R_L = 100 \text{ k}\Omega$		85°C		0.47		,,
SR	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.56		V/μs
		Joseph	V _{I(PP)} = 5.5 V	-40°C		0.70		
			, ,	85°C		0.44		
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$,	25°C		32		nV/√ Hz
				25°C		35		
Вом	Maximum output-swing bandwidth	$V_O = V_{OH}$, $R_L = 100 \text{ k}\Omega$,		-40°C		45		kHz
			See rigule r	85°C		25		
				25°C		635		
В1	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	$C_L = 20 pF$,	−40°C		880		kHz
		See Figure 3		85°C		480		
				25°C		43°		
φ _m Phase margin	Phase margin	$V_{I} = 10 \text{ mV},$ $C_{I} = 20 \text{ pF},$	f = B ₁ , See Figure 3	-40°C		46°		
		ο _L = 20 pr,	occ rigule 3	85°C		41°		

TLC27M2, TLC27M2A, TLC27M2B, TLC27M7 LinCMOS™ PRECISION DUAL OPERATIONAL AMPLIFIERS

SLOS051E - OCTOBER 1987 - REVISED AUGUST 2008

operating characteristics at specified free-air temperature, $V_{DD} = 5 V$

	PARAMETER	TEST CO	ONDITIONS	TA		.C27M2I .C27M7I		UNIT
					MIN	TYP	MAX	
				25°C		0.43		
			V _{I(PP)} = 1 V	−55°C		0.54		
CD.		$R_L = 100 \text{ k}\Omega$, ,	125°C		0.29		.,,
SR	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.40		V/μs
		l coo : iguio :	V _{I(PP)} = 2.5 V	−55°C		0.49		
			, ,	125°C		0.28		
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$,	25°C		32		nV/√ Hz
			_	25°C		55		
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH}$, $R_L = 100 \text{ k}\Omega$,		−55°C		80		kHz
			occ rigure r	125°C		40		
				25°C		525		
В1	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	$C_L = 20 pF$,	−55°C		850		kHz
		occ rigare s		125°C		330		
		.,,	, _	25°C		40°		
φm	Phase margin	$V_{\parallel} = 10 \text{ mV},$	f = B ₁ , See Figure 3	−55°C		44°		
		OL - 20 pr,	Occ i iguic 3	125°C		36°		

operating characteristics at specified free-air temperature, V_{DD} = 10 V

	PARAMETER	TEST CO	ONDITIONS	TA		.C27M2I .C27M7I		UNIT	
					MIN	TYP	MAX		
				25°C		0.62			
			V _{I(PP)} = 1 V	−55°C		0.81			
	Olements at with main	$R_L = 100 \text{ k}\Omega$. ,	125°C		0.38		\// -	
SR	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.56		V/μs	
	$V_{I(PP)} = 5.5 \text{ V}$ -55°C 125°C		0.73						
			, ,	125°C		0.35			
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$,	25°C		32		nV/√ Hz	
		VO = VOH,	_	25°C		35			
ВОМ	Maximum output-swing bandwidth		C _L = 20 pF, See Figure 1	−55°C		50		kHz	
		K_ = 100 KS2,	See Figure 1	125°C		20			
			_	25°C		635			
В1	Unity gain bandwidth	V _I = 10 mV, See Figure 3	$C_L = 20 pF$,	−55°C		960		kHz	
		See rigure 3		125°C		440			
			, _	25°C		43°			
φm	Phase margin	$V_{I} = 10 \text{ mV},$	f = B ₁ , See Figure 3	−55°C		47°			
		OL = 20 pr,	See Figure 3	125°C		39°			

PARAMETER MEASUREMENT INFORMATION

single-supply versus split-supply test circuits

Because the TLC27M2 and TLC27M7 are optimized for single-supply operation, circuit configurations used for the various tests often present some inconvenience since the input signal, in many cases, must be offset from ground. This inconvenience can be avoided by testing the device with split supplies and the output load tied to the negative rail. A comparison of single-supply versus split-supply test circuits is shown below. The use of either circuit gives the same result.

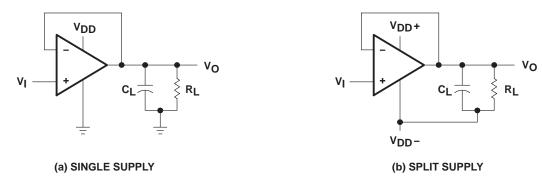


Figure 1. Unity-Gain Amplifier

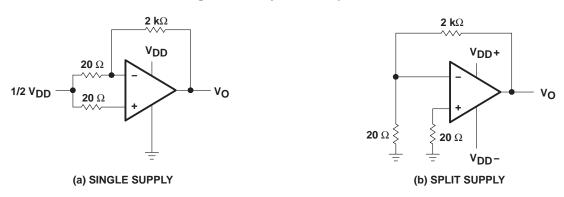


Figure 2. Noise-Test Circuit

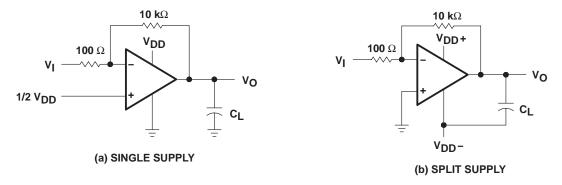


Figure 3. Gain-of-100 Inverting Amplifier

SLOS051E - OCTOBER 1987 - REVISED AUGUST 2008

PARAMETER MEASUREMENT INFORMATION

input bias current

Because of the high input impedance of the TLC27M2 and TLC27M7 operational amplifiers, attempts to measure the input bias current can result in erroneous readings. The bias current at normal room ambient temperature is typically less than 1 pA, a value that is easily exceeded by leakages on the test socket. Two suggestions are offered to avoid erroneous measurements:

- 1. Isolate the device from other potential leakage sources. Use a grounded shield around and between the device inputs (see Figure 4). Leakages that would otherwise flow to the inputs are shunted away.
- Compensate for the leakage of the test socket by actually performing an input bias current test (using a picoammeter) with no device in the test socket. The actual input bias current can then be calculated by subtracting the open-socket leakage readings from the readings obtained with a device in the test socket.

One word of caution—many automatic testers as well as some bench-top operational amplifier testers use the servo-loop technique with a resistor in series with the device input to measure the input bias current (the voltage drop across the series resistor is measured and the bias current is calculated). This method requires that a device be inserted into the test socket to obtain a correct reading; therefore, an open-socket reading is not feasible using this method.

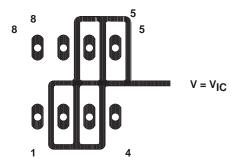


Figure 4. Isolation Metal Around Device Inputs (JG and P packages)

low-level output voltage

To obtain low-supply-voltage operation, some compromise was necessary in the input stage. This compromise results in the device low-level output being dependent on both the common-mode input voltage level as well as the differential input voltage level. When attempting to correlate low-level output readings with those quoted in the electrical specifications, these two conditions should be observed. If conditions other than these are to be used, please refer to Figures 14 through 19 in the Typical Characteristics of this data sheet.

SLOS051E - OCTOBER 1987 - REVISED AUGUST 2008

PARAMETER MEASUREMENT INFORMATION

input offset voltage temperature coefficient

Erroneous readings often result from attempts to measure temperature coefficient of input offset voltage. This parameter is actually a calculation using input offset voltage measurements obtained at two different temperatures. When one (or both) of the temperatures is below freezing, moisture can collect on both the device and the test socket. This moisture results in leakage and contact resistance, which can cause erroneous input offset voltage readings. The isolation techniques previously mentioned have no effect on the leakage, since the moisture also covers the isolation metal itself, thereby rendering it useless. It is suggested that these measurements be performed at temperatures above freezing to minimize error.

full-power response

Full-power response, the frequency above which the operational amplifier slew rate limits the output voltage swing, is often specified two ways: full-linear response and full-peak response. The full-linear response is generally measured by monitoring the distortion level of the output while increasing the frequency of a sinusoidal input signal until the maximum frequency is found above which the output contains significant distortion. The full-peak response is defined as the maximum output frequency, without regard to distortion, above which full peak-to-peak output swing cannot be maintained.

Because there is no industry-wide accepted value for significant distortion, the full-peak response is specified in this data sheet and is measured using the circuit of Figure 1. The initial setup involves the use of a sinusoidal input to determine the maximum peak-to-peak output of the device (the amplitude of the sinusoidal wave is increased until clipping occurs). The sinusoidal wave is then replaced with a square wave of the same amplitude. The frequency is then increased until the maximum peak-to-peak output can no longer be maintained (Figure 5). A square wave is used to allow a more accurate determination of the point at which the maximum peak-to-peak output is reached.

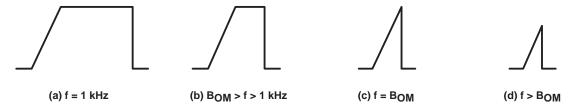


Figure 5. Full-Power-Response Output Signal

test time

Inadequate test time is a frequent problem, especially when testing CMOS devices in a high-volume, short-test-time environment. Internal capacitances are inherently higher in CMOS than in bipolar and BiFET devices and require longer test times than their bipolar and BiFET counterparts. The problem becomes more pronounced with reduced supply levels and lower temperatures.

TLC27M2, TLC27M2A, TLC27M2B, TLC27M7 LinCMOS™ PRECISION DUAL OPERATIONAL AMPLIFIERS

SLOS051E - OCTOBER 1987 - REVISED AUGUST 2008

TYPICAL CHARACTERISTICS

Table of Graphs

			FIGURE
V _{IO}	Input offset voltage	Distribution	6, 7
lpha VIO	Temperature coefficient	Distribution	8, 9
VOH	High-level output voltage	vs High-level output current vs Supply voltage vs Free-air temperature	10, 11 12 13
V _{OL}	Low-level output voltage	vs Common-mode input voltage vs Differential input voltage vs Free-air temperature vs Low-level output current	14, 15 16 17 18, 19
AVD	Differential voltage amplification	vs Supply voltage vs Free-air temperature vs Frequency	20 21 32, 33
I _{IB} /I _{IO}	Input bias and input offset current	vs Free-air temperature	22
VIC	Common-mode input voltage	vs Supply voltage	23
I _{DD}	Supply current	vs Supply voltage vs Free-air temperature	24 25
SR	Slew rate	vs Supply voltage vs Free-air temperature	26 27
	Normalized slew rate	vs Free-air temperature	28
VO(PP)	Maximum peak-to-peak output voltage	vs Frequency	29
B ₁	Unity-gain bandwidth	vs Free-air temperature vs Supply voltage	30 31
φm	Phase margin	vs Supply voltage vs Free-air temperature vs Capacitive loads	34 35 36
Vn	Equivalent input noise voltage	vs Frequency	37
ф	Phase shift	vs Frequency	32, 33

TYPICAL CHARACTERISTICS

DISTRIBUTION OF TLC27M2 INPUT OFFSET VOLTAGE

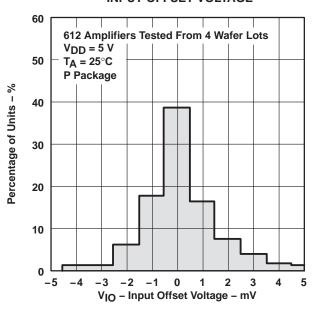


Figure 6

DISTRIBUTION OF TLC27M2 INPUT OFFSET VOLTAGE

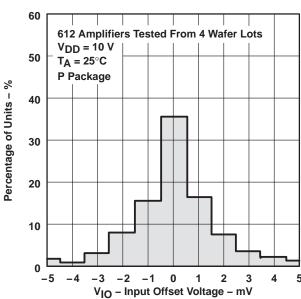


Figure 7

DISTRIBUTION OF TLC27M2 AND TLC27M7 INPUT OFFSET VOLTAGE TEMPERATURE COEFFICIENT

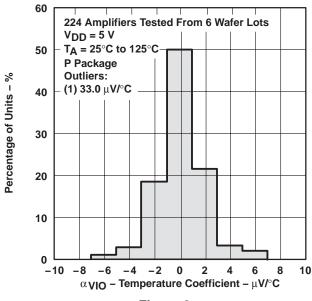


Figure 8

DISTRIBUTION OF TLC27M2 AND TLC27M7 INPUT OFFSET VOLTAGE TEMPERATURE COEFFICIENT

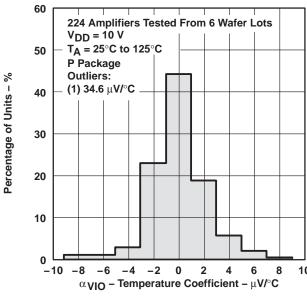
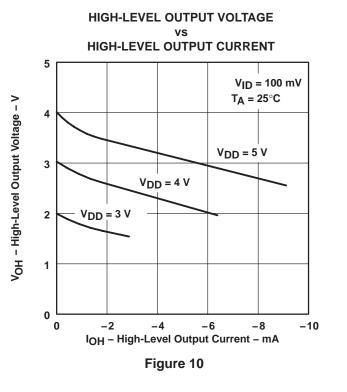
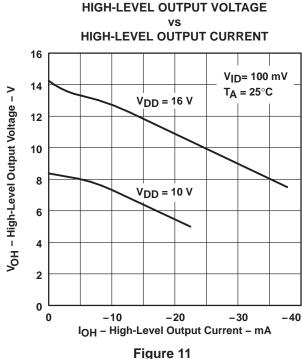
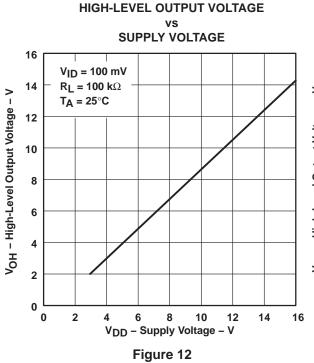


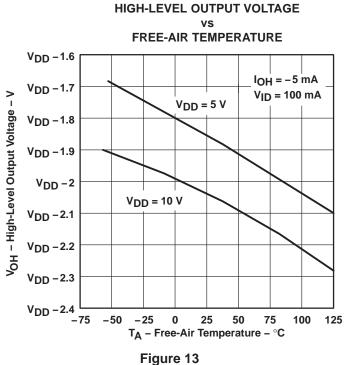
Figure 9

TYPICAL CHARACTERISTICS[†]





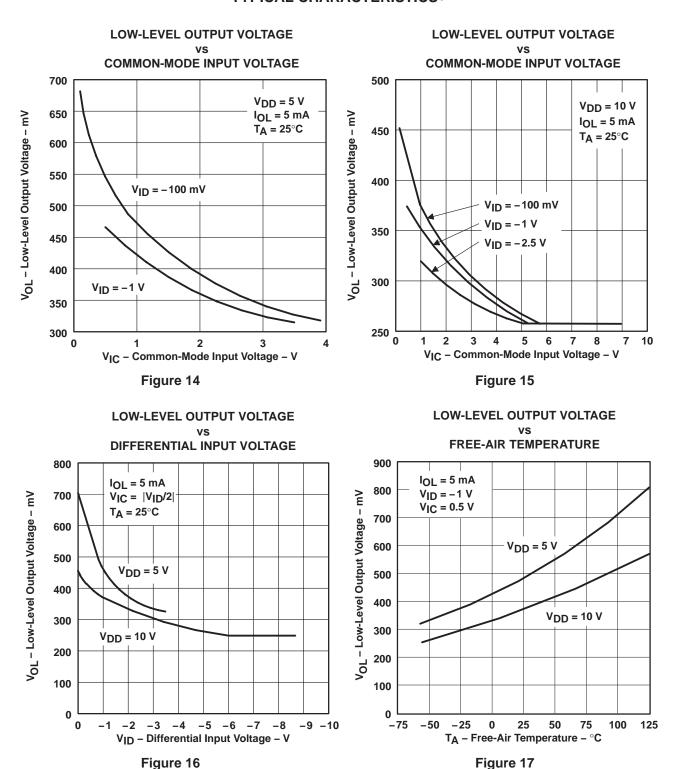




[†]Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



TYPICAL CHARACTERISTICS[†]

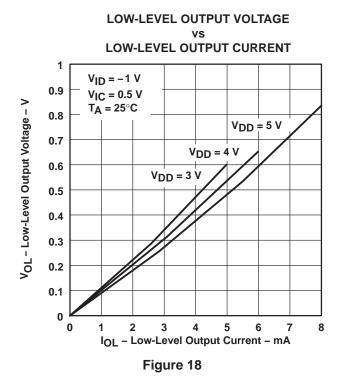


[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



LOW-LEVEL OUTPUT VOLTAGE

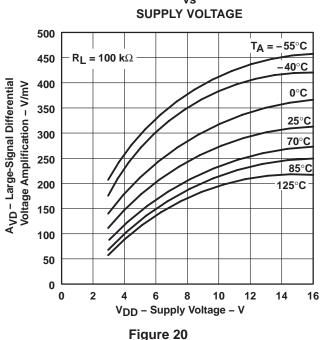
TYPICAL CHARACTERISTICS[†]



LOW-LEVEL OUTPUT CURRENT 3 $V_{ID} = -1 V$ VoL - Low-Level Output Voltage - V $V_{IC} = 0.5 V$ 2.5 V_{DD} = 16 V T_A = 25°C 2 $V_{DD} = 10 V$ 1.5 1 0.5 0 0 15 20 25 30 IOL - Low-Level Output Current - mA

Figure 19

LARGE-SIGNAL
DIFFERENTIAL VOLTAGE AMPLIFICATION
vs
SUPPLY VOLTAGE



LARGE-SIGNAL
DIFFERENTIAL VOLTAGE AMPLIFICATION
vs

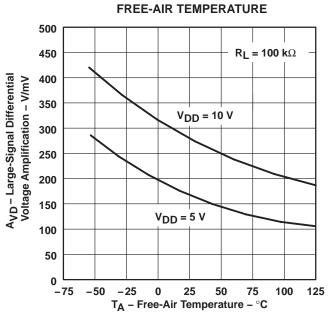


Figure 21

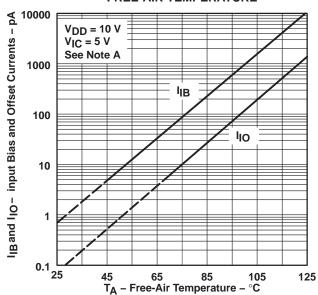
†Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



TYPICAL CHARACTERISTICS[†]

INPUT BIAS CURRENT AND INPUT OFFSET **CURRENT**

vs FREE-AIR TEMPERATURE



NOTE A: The typical values of input bias current and input offset current below 5 pA were determined mathematically.

Figure 22

SUPPLY CURRENT vs **SUPPLY VOLTAGE**

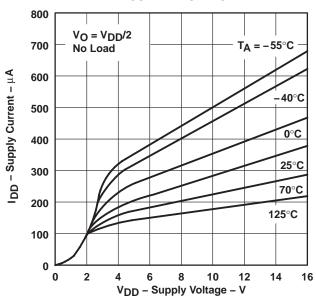


Figure 24

COMMON-MODE INPUT VOLTAGE POSITIVE LIMIT vs

SUPPLY VOLTAGE

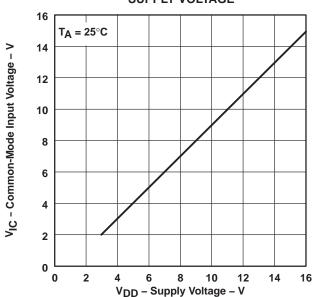


Figure 23

SUPPLY CURRENT

vs FREE-AIR TEMPERATURE

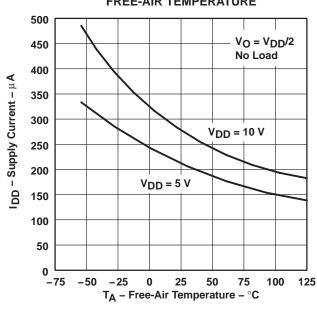


Figure 25

[†]Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



 $A_V = 1$

 $R_L = 100 \text{ k}\Omega$

See Figure 1

 $V_{DD} = 10 V$

 $V_{I(PP)} = 1 V$

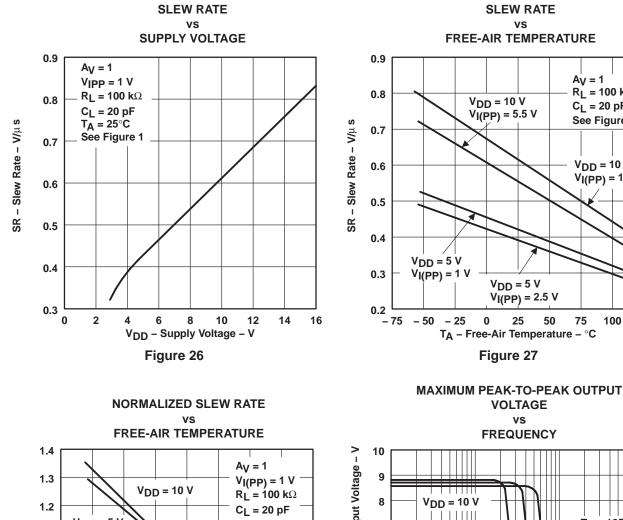
75

100

125

C_L = 20 pF

TYPICAL CHARACTERISTICS[†]



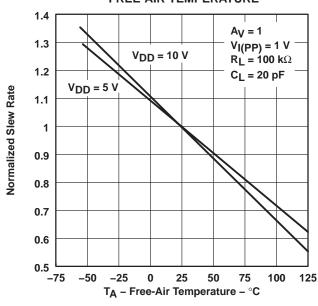
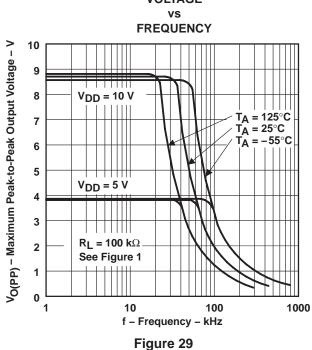


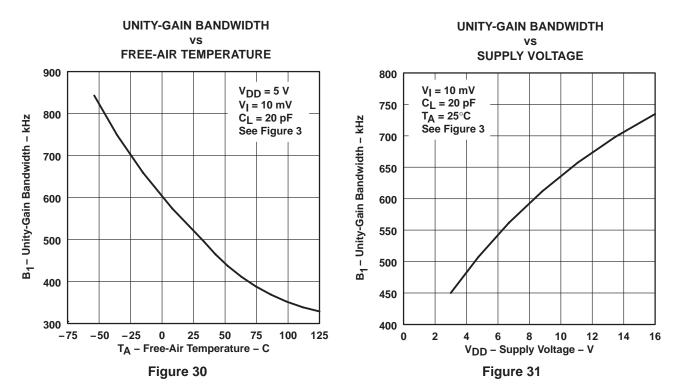
Figure 28



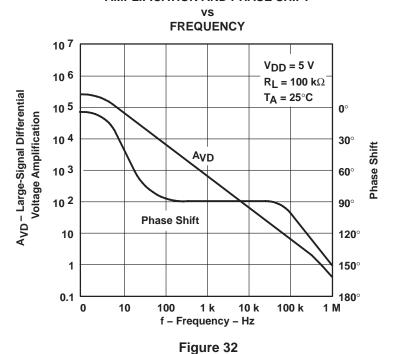
[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



TYPICAL CHARACTERISTICS[†]



LARGE-SCALE DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT



[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



TYPICAL CHARACTERISTICS[†]

LARGE-SCALE DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT

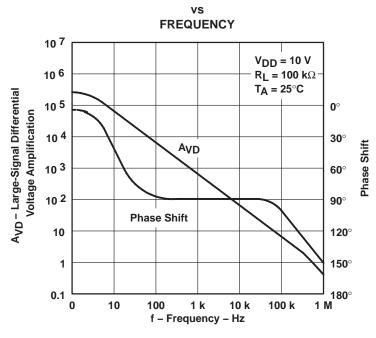
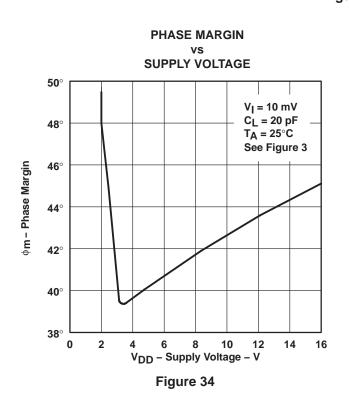
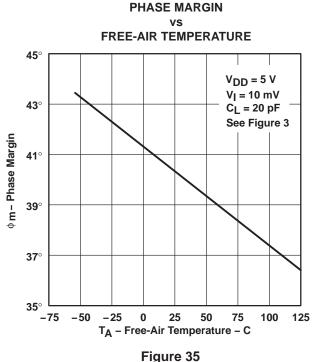


Figure 33





[†]Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



TYPICAL CHARACTERISTICS

PHASE MARGIN vs CAPACITIVE LOAD

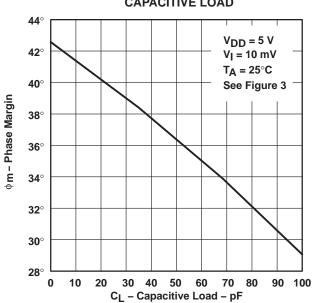


Figure 36

EQUIVALENT INPUT NOISE VOLTAGE

FREQUENCY

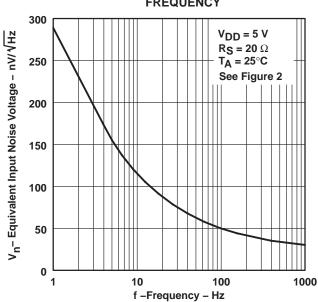


Figure 37

single-supply operation

While the TLC27M2 and TLC27M7 perform well using dual power supplies (also called balanced or split supplies), the design is optimized for single-supply operation. This design includes an input common-mode voltage range that encompasses ground, as well as an output voltage range that pulls down to ground. The supply voltage range extends down to 3 V (C-suffix types), thus allowing operation with supply levels commonly available for TTL and HCMOS; however, for maximum dynamic range, 16-V single-supply operation is recommended.

Many single-supply applications require that a voltage be applied to one input to establish a reference level that is above ground. A resistive voltage divider is usually sufficient to establish this reference level (see Figure 38). The low input bias current of the TLC27M2 and TLC27M7 permits the use of very large resistive values to implement the voltage divider, thus minimizing power consumption.

The TLC27M2 and TLC27M7 work well in conjunction with digital logic; however, when powering both linear devices and digital logic from the same power supply, the following precautions are recommended:

- 1. Power the linear devices from separate bypassed supply lines (see Figure 39); otherwise, the linear device supply rails can fluctuate due to voltage drops caused by high switching currents in the digital logic.
- 2. Use proper bypass techniques to reduce the probability of noise-induced errors. Single capacitive decoupling is often adequate; however, high-frequency applications may require RC decoupling.

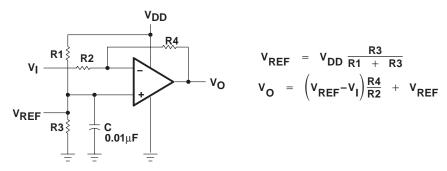
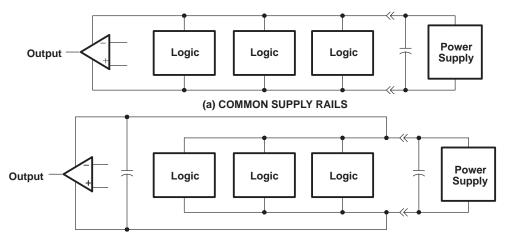


Figure 38. Inverting Amplifier With Voltage Reference



(b) SEPARATE BYPASSED SUPPLY RAILS (preferred)

Figure 39. Common Versus Separate Supply Rails



SLOS051E - OCTOBER 1987 - REVISED AUGUST 2008

APPLICATION INFORMATION

input characteristics

The TLC27M2 and TLC27M7 are specified with a minimum and a maximum input voltage that, if exceeded at either input, could cause the device to malfunction. Exceeding this specified range is a common problem, especially in single-supply operation. Note that the lower range limit includes the negative rail, while the upper range limit is specified at V_{DD} –1 V at T_A = 25°C and at V_{DD} –1.5 V at all other temperatures.

The use of the polysilicon-gate process and the careful input circuit design gives the TLC27M2 and TLC27M7 very good input offset voltage drift characteristics relative to conventional metal-gate processes. Offset voltage drift in CMOS devices is highly influenced by threshold voltage shifts caused by polarization of the phosphorus dopant implanted in the oxide. Placing the phosphorus dopant in a conductor (such as a polysilicon gate) alleviates the polarization problem, thus reducing threshold voltage shifts by more than an order of magnitude. The offset voltage drift with time has been calculated to be typically 0.1 μ V/month, including the first month of operation.

Because of the extremely high input impedance and resulting low bias current requirements, the TLC27M2 and TLC27M7 are well suited for low-level signal processing; however, leakage currents on printed-circuit boards and sockets can easily exceed bias current requirements and cause a degradation in device performance. It is good practice to include guard rings around inputs (similar to those of Figure 4 in the Parameter Measurement Information section). These guards should be driven from a low-impedance source at the same voltage level as the common-mode input (see Figure 40).

The inputs of any unused amplifiers should be tied to ground to avoid possible oscillation.

noise performance

The noise specifications in operational amplifier circuits are greatly dependent on the current in the first-stage differential amplifier. The low input bias current requirements of the TLC27M2 and TLC27M7 result in a very low noise current, which is insignificant in most applications. This feature makes the devices especially favorable over bipolar devices when using values of circuit impedance greater than 50 k Ω , since bipolar devices exhibit greater noise currents.

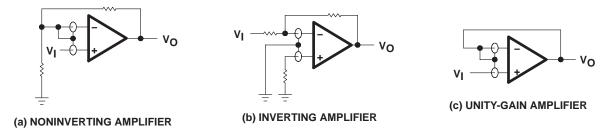


Figure 40. Guard-Ring Schemes

output characteristics

The output stage of the TLC27M2 and TLC27M7 is designed to sink and source relatively high amounts of current (see typical characteristics). If the output is subjected to a short-circuit condition, this high current capability can cause device damage under certain conditions. Output current capability increases with supply voltage.

All operating characteristics of the TLC27M2 and TLC27M7 were measured using a 20-pF load. The devices drive higher capacitive loads; however, as output load capacitance increases, the resulting response pole occurs at lower frequencies, thereby causing ringing, peaking, or even oscillation (see Figure 41). In many cases, adding a small amount of resistance in series with the load capacitance alleviates the problem.



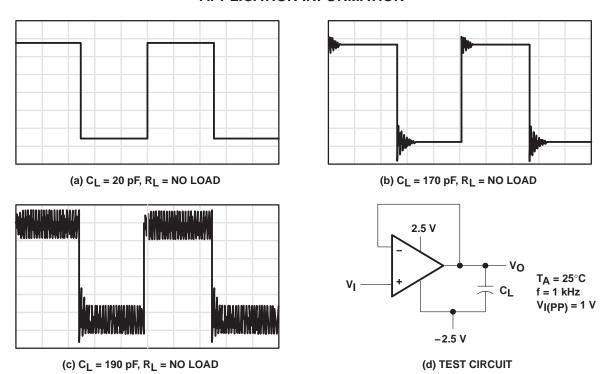
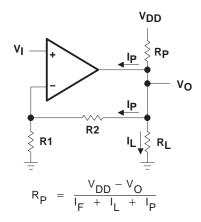


Figure 41. Effect of Capacitive Loads and Test Circuit

output characteristics (continued)

Although the TLC27M2 and TLC27M7 possess excellent high-level output voltage and current capability, methods for boosting this capability are available, if needed. The simplest method involves the use of a pullup resistor (R_P) connected from the output to the positive supply rail (see Figure 42). There are two disadvantages to the use of this circuit. First, the NMOS pulldown transistor N4 (see equivalent schematic) must sink a comparatively large amount of current. In this circuit, N4 behaves like a linear resistor with an on-resistance between approximately 60 Ω and 180 Ω , depending on how hard the operational amplifier input is driven. With very low values of R_P, a voltage offset from 0 V at the output occurs. Second, pullup resistor R_P acts as a drain load to N4 and the gain of the operational amplifier is reduced at output voltage levels where N5 is not supplying the output current.

output characteristics (continued)



Ip = Pullup current required by the operational amplifier (typically 500 μ A)

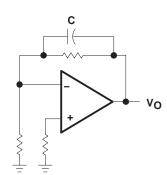


Figure 43. Compensation for Input Capacitance

Figure 42. Resistive Pullup to Increase VOH

feedback

Operational amplifier circuits nearly always employ feedback, and since feedback is the first prerequisite for oscillation, some caution is appropriate. Most oscillation problems result from driving capacitive loads (discussed previously) and ignoring stray input capacitance. A small-value capacitor connected in parallel with the feedback resistor is an effective remedy (see Figure 43). The value of this capacitor is optimized empirically.

electrostatic-discharge protection

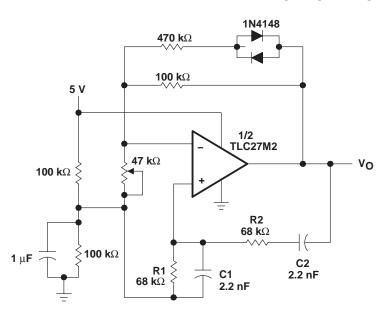
The TLC27M2 and TLC27M7 incorporate an internal electrostatic-discharge (ESD) protection circuit that prevents functional failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015.2. Care should be exercised, however, when handling these devices as exposure to ESD may result in the degradation of the device parametric performance. The protection circuit also causes the input bias currents to be temperature dependent and have the characteristics of a reverse-biased diode.

latch-up

Because CMOS devices are susceptible to latch-up due to their inherent parasitic thyristors, the TLC27M2 and TLC27M7 inputs and outputs were designed to withstand -100-mA surge currents without sustaining latch-up; however, techniques should be used to reduce the chance of latch-up whenever possible. Internal protection diodes should not, by design, be forward biased. Applied input and output voltage should not exceed the supply voltage by more than 300 mV. Care should be exercised when using capacitive coupling on pulse generators. Supply transients should be shunted by the use of decoupling capacitors (0.1 μ F typical) located across the supply rails as close to the device as possible.

The current path established if latch-up occurs is usually between the positive supply rail and ground and can be triggered by surges on the supply lines and/or voltages on either the output or inputs that exceed the supply voltage. Once latch-up occurs, the current flow is limited only by the impedance of the power supply and the forward resistance of the parasitic thyristor and usually results in the destruction of the device. The chance of latch-up occurring increases with increasing temperature and supply voltages.





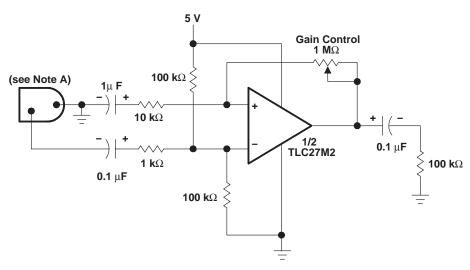
NOTES:
$$V_{O(PP)} \approx 2 V$$

 $f_{O} = \frac{1}{2\pi \sqrt{R1R2C1C2}}$

Figure 44. Wien Oscillator

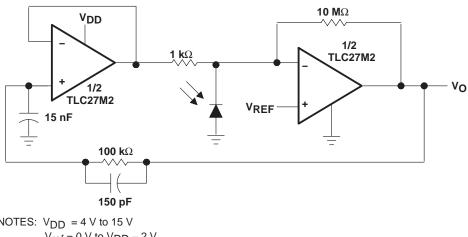
NOTES: $V_I = 0 \text{ V to } 3 \text{ V}$ $I_S = \frac{V_I}{R}$

Figure 45. Precision Low-Current Sink



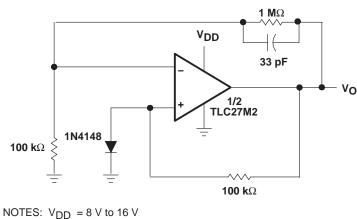
NOTE A: Low to medium impedance dynamic mike

Figure 46. Microphone Preamplifier



NOTES: $V_{DD} = 4 \text{ V to } 15 \text{ V}$ $V_{ref} = 0 V to V_{DD} - 2 V$

Figure 47. Photo-Diode Amplifier With Ambient Light Rejection



 $V_0 = 5 \text{ V}, 10 \text{ mA}$

Figure 48. 5-V Low-Power Voltage Regulator

SLOS051E - OCTOBER 1987 - REVISED AUGUST 2008

APPLICATION INFORMATION

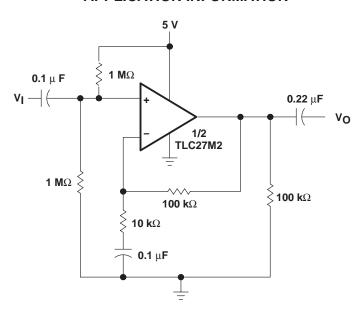


Figure 49. Single-Rail AC Amplifiers





10-Jun-2014

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish (6)	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TLC27M2ACD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27M2AC	Samples
TLC27M2ACDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27M2AC	Samples
TLC27M2ACDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27M2AC	Samples
TLC27M2ACP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC27M2AC	Samples
TLC27M2ACPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC27M2AC	Samples
TLC27M2AID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27M2AI	Samples
TLC27M2AIDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27M2AI	Samples
TLC27M2AIDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27M2AI	Samples
TLC27M2AIDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27M2AI	Samples
TLC27M2AIP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TLC27M2AI	Samples
TLC27M2BCD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27M2BC	Samples
TLC27M2BCDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27M2BC	Samples
TLC27M2BCDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27M2BC	Samples
TLC27M2BCDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27M2BC	Samples
TLC27M2BCP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC27M2BC	Samples
TLC27M2BID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27M2BI	Samples
TLC27M2BIDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27M2BI	Samples





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Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
TLC27M2BIDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27M2BI	Samples
TLC27M2BIDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27M2BI	Samples
TLC27M2BIP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TLC27M2BI	Samples
TLC27M2CD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27M2C	Samples
TLC27M2CDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27M2C	Samples
TLC27M2CDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27M2C	Samples
TLC27M2CDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27M2C	Sample
TLC27M2CP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC27M2CP	Sample
TLC27M2CPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC27M2CP	Sample
TLC27M2CPSLE	OBSOLETE	SO	PS	8		TBD	Call TI	Call TI	0 to 70		
TLC27M2CPSR	ACTIVE	SO	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	P27M2	Sample
TLC27M2CPSRG4	ACTIVE	SO	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	P27M2	Sample
TLC27M2CPW	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	P27M2	Sample
TLC27M2CPWLE	OBSOLETE	TSSOP	PW	8		TBD	Call TI	Call TI	0 to 70		
TLC27M2CPWR	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	P27M2	Sample
TLC27M2CPWRG4	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	P27M2	Sample
TLC27M2ID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27M2I	Sample
TLC27M2IDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27M2I	Sample
TLC27M2IDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27M2I	Sample





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Orderable Device		Package Type	Package Drawing		Package Qty		Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Sample
TI 00=110 DD 0.4	(1)					(2)	(6)	(3)		(4/5)	
TLC27M2IDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27M2I	Sample
TLC27M2IP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TLC27M2IP	Sample
TLC27M2IPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TLC27M2IP	Sample
TLC27M2IPW	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	P27M2I	Sample
TLC27M2IPWG4	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	P27M2I	Sample
TLC27M2IPWR	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	P27M2I	Sample
TLC27M2IPWRG4	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	P27M2I	Sample
TLC27M2MD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	27M2M	Sampl
TLC27M2MDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	27M2M	Sampl
TLC27M2MFKB	OBSOLETE	LCCC	FK	20		TBD	Call TI	Call TI	-55 to 125		
TLC27M2MJG	OBSOLETE	CDIP	JG	8		TBD	Call TI	Call TI	-55 to 125		
TLC27M2MJGB	OBSOLETE	CDIP	JG	8		TBD	Call TI	Call TI	-55 to 125		
TLC27M7CD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27M7C	Sampl
TLC27M7CDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27M7C	Sampl
TLC27M7CDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27M7C	Sampl
TLC27M7CDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27M7C	Sampl
TLC27M7CP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC27M7CP	Samp
TLC27M7CPSR	ACTIVE	SO	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	P27M7	Samp
TLC27M7ID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27M7I	Samp



PACKAGE OPTION ADDENDUM

10-Jun-2014

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
TLC27M7IDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27M7I	Samples
TLC27M7IDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27M7I	Samples
TLC27M7IDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27M7I	Samples
TLC27M7IP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TLC27M7IP	Samples
TLC27M7IPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TLC27M7IP	Samples
TLC27M7MFKB	OBSOLETE	E LCCC	FK	20		TBD	Call TI	Call TI	-55 to 125		
TLC27M7MJG	OBSOLETE	CDIP	JG	8		TBD	Call TI	Call TI	-55 to 125		
TLC27M7MJGB	OBSOLETE	CDIP	JG	8		TBD	Call TI	Call TI	-55 to 125		
TLC27M7MUB	OBSOLETE	E CFP	U	10		TBD	Call TI	Call TI	-55 to 125		

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.



PACKAGE OPTION ADDENDUM

10-Jun-2014

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

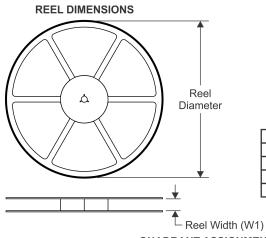
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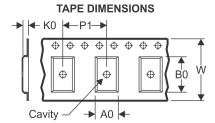
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PACKAGE MATERIALS INFORMATION

www.ti.com 8-Jul-2013

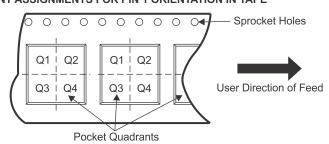
TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

'All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLC27M2ACDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC27M2AIDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC27M2BCDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC27M2BIDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC27M2CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC27M2CPSR	SO	PS	8	2000	330.0	16.4	8.2	6.6	2.5	12.0	16.0	Q1
TLC27M2CPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
TLC27M2IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC27M7CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC27M7CPSR	SO	PS	8	2000	330.0	16.4	8.2	6.6	2.5	12.0	16.0	Q1
TLC27M7IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

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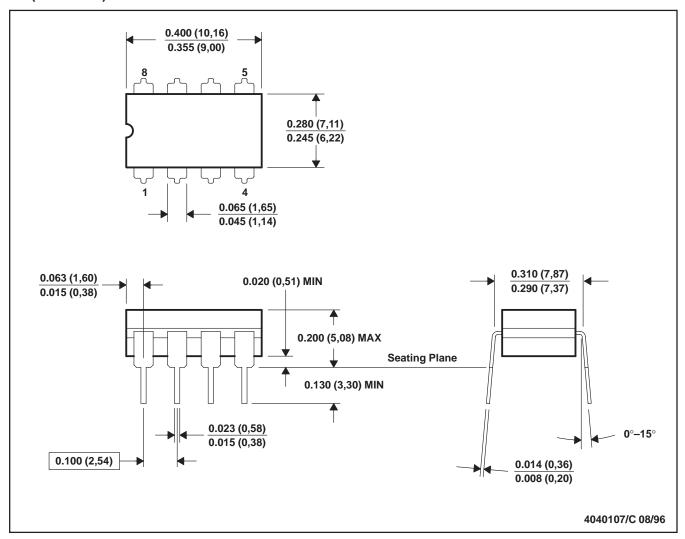


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLC27M2ACDR	SOIC	D	8	2500	340.5	338.1	20.6
TLC27M2AIDR	SOIC	D	8	2500	340.5	338.1	20.6
TLC27M2BCDR	SOIC	D	8	2500	340.5	338.1	20.6
TLC27M2BIDR	SOIC	D	8	2500	340.5	338.1	20.6
TLC27M2CDR	SOIC	D	8	2500	340.5	338.1	20.6
TLC27M2CPSR	SO	PS	8	2000	367.0	367.0	38.0
TLC27M2CPWR	TSSOP	PW	8	2000	367.0	367.0	35.0
TLC27M2IDR	SOIC	D	8	2500	340.5	338.1	20.6
TLC27M7CDR	SOIC	D	8	2500	340.5	338.1	20.6
TLC27M7CPSR	SO	PS	8	2000	367.0	367.0	38.0
TLC27M7IDR	SOIC	D	8	2500	340.5	338.1	20.6

JG (R-GDIP-T8)

CERAMIC DUAL-IN-LINE

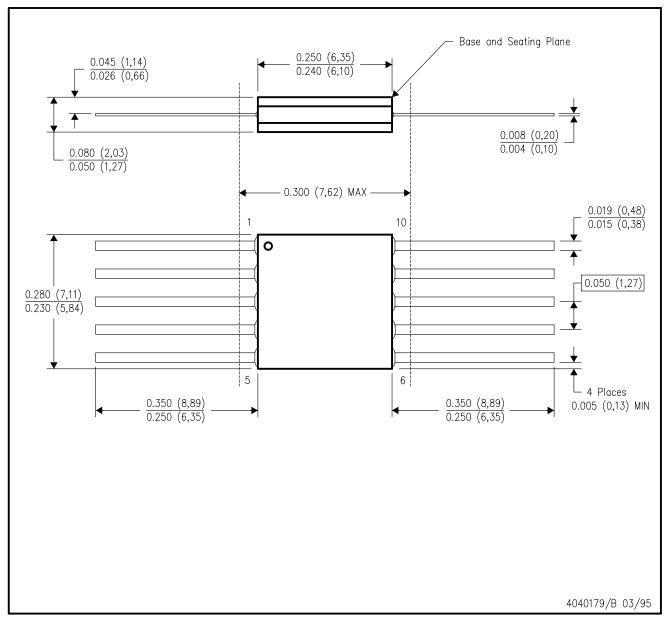


NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification.
- E. Falls within MIL STD 1835 GDIP1-T8

U (S-GDFP-F10)

CERAMIC DUAL FLATPACK



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only.
- E. Falls within MIL STD 1835 GDFP1-F10 and JEDEC MO-092AA



FK (S-CQCC-N**)

LEADLESS CERAMIC CHIP CARRIER

28 TERMINAL SHOWN

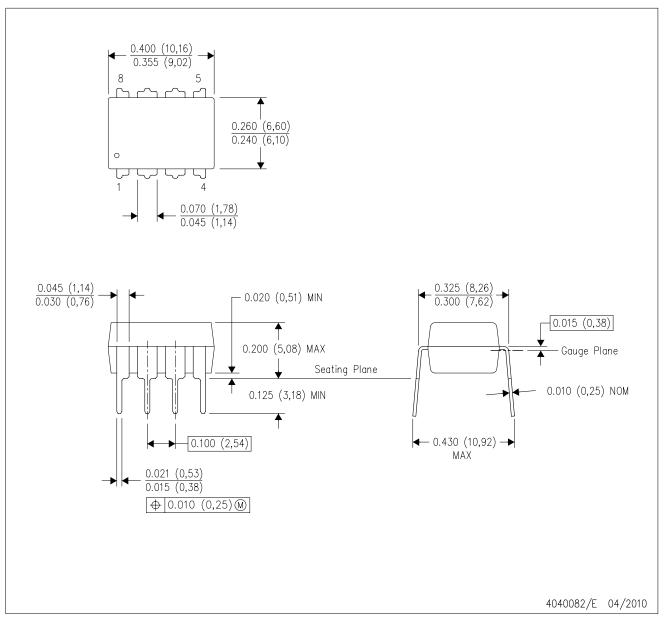


- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a metal lid.
- D. Falls within JEDEC MS-004



P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.





NOTES: A. All linear dimensions are in millimeters.

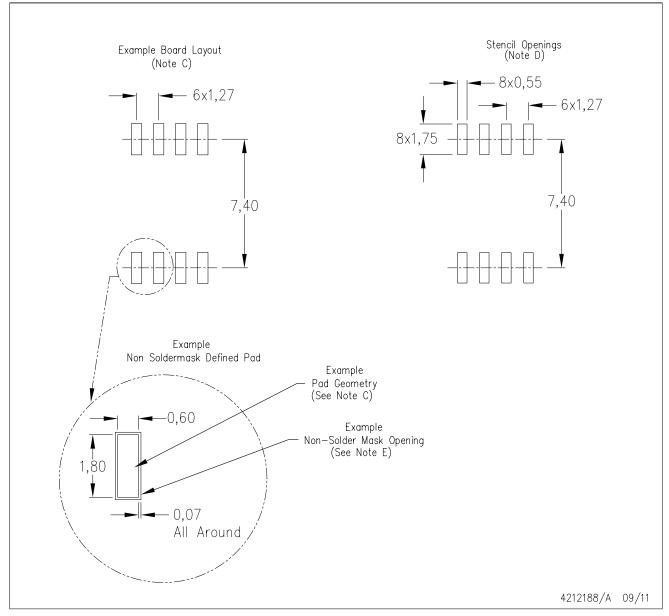
B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



PS (R-PDSO-G8)

PLASTIC SMALL OUTLINE

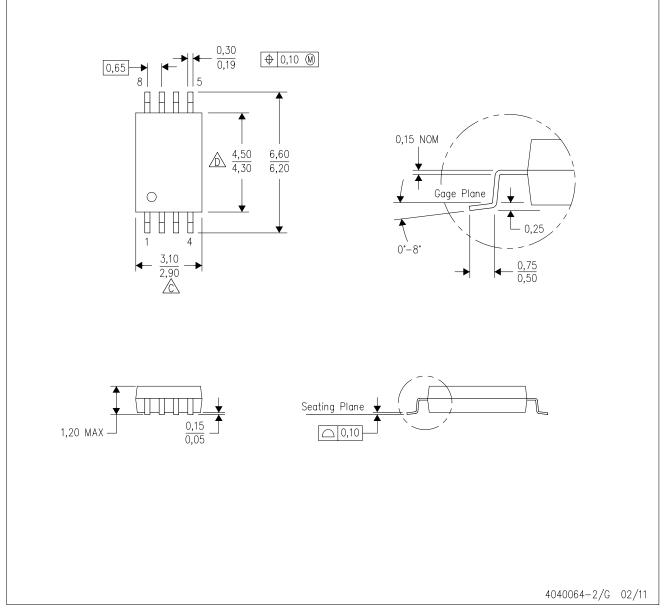


- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



PW (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



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